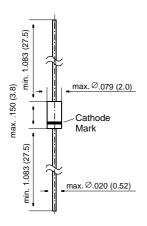
## **BAT42**, **BAT43**

### **Schottky Diodes**

#### **DO-35**



Dimensions in inches and (millimeters)

#### **FEATURES**

- For general purpose applications
- These diodes feature very low turnon voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- These diodes are also available in the SOD-123 case with the type designations BAT42W to BAT43W and in the MiniMELF case with type designations LL42 to LL43.

#### **MECHANICAL DATA**

Case: DO-35 Glass Case Weight: approx. 0.13 g

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit	
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	30	V	
Forward Continuous Current at T <sub>amb</sub> = 25 °C	lF	2001)	mA	
Repetitive Peak Forward Current at $t_p < 1$ s, $\delta < 0.5$ , $T_{amb} = 25$ °C	I <sub>FRM</sub>	500 <sup>1)</sup>	mA	
Surge Forward Current at t <sub>p</sub> < 10 ms, T <sub>amb</sub> = 25 °C	I <sub>FSM</sub>	41)	Α	
Power Dissipation <sup>1)</sup> at T <sub>amb</sub> = 65 °C	P <sub>tot</sub>	2001)	mW	
Junction Temperature	Tj	125	°C	
Ambient Operating Temperature Range	T <sub>amb</sub>	-65 to +125	°C	
Storage Temperature Range	T <sub>S</sub>	-65 to +150	°C	

1) Valid provided that leads at a distance of 4 mm from case are kept at ambient temperature



# **BAT42**, **BAT43**

#### **ELECTRICAL CHARACTERISTICS**

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Тур.	Max.	Unit
Reverse Breakdown Voltage tested with 100 μA Pulses	V <sub>(BR)R</sub>	30	-	_	V
at $I_F = 50 \text{ mA}$ at $I_F = 2 \text{ mA}$ BA	V <sub>F</sub> T42 V <sub>F</sub> T42 V <sub>F</sub> T43 V <sub>F</sub> T43 V <sub>F</sub>	- - - 0.26	- - - -	1 0.4 0.65 0.33 0.45	V V V V
Leakage Current Pulse Test $t_p < 300 \ \mu s, \ \delta < 2\%$ at $V_R = 25 \ V$ at $V_R = 25 \ V$ , $T_j = 100 \ ^{\circ}C$	I <sub>R</sub>	_	=	0.5 100	μ <b>Α</b> μ <b>Α</b>
Capacitance at $V_R = 1 \text{ V, f} = 1 \text{ MHz}$	C <sub>tot</sub>	-	7	_	pF
Reverse Recovery Time from $I_F$ = 10 mA through $I_R$ = 10 mA to $I_R$ = 1 R <sub>L</sub> = 100 $\Omega$	mA, t <sub>rr</sub>	_	_	5	ns
Detection Efficiency at $R_L$ = 15 K $\Omega$ , $C_L$ = 300 pF, $f$ = 45 MHz, $V_{RF}$ = 2 V	ην	80	-	-	%
Thermal Resistance Junction to Ambient A	r R <sub>thJA</sub>	_	_	0.31)	K/mW

<sup>1)</sup> Valid provided that leads at a distance of 4 mm from the case are kept at ambient temperature

